



**BU407**

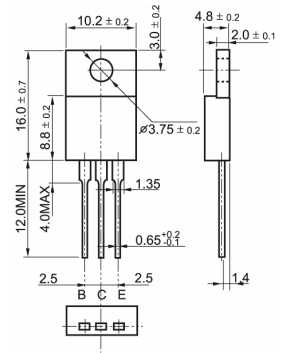
**SILICON EPITAXIAL PLANNAR TRANSISTOR**

**GENERAL DESCRIPTION**

High frequency, high power transistors in a plastic envelope, primarily for use in audio and general purpose



TO-220



**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0V$		330	V
$V_{CEO}$	Collector-emitter voltage (open base)			150	V
$I_C$	Collector current (DC)			7	A
$I_{CM}$	Collector current peak value			15	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25^\circ C$		60	W
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = 5.0A; I_B = 0.5A$		1.0	V
$V_F$	Diode forward voltage				V
$t_f$	Fall time	$I_C=5A, -I_{B(end)}=0.5A, V_{CC}=60V$		0.75	$\mu s$

**LIMITING VALUES**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0V$	-	330	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	150	V
$V_{EBO}$	Emitter-base voltage (open collector)			5	V
$I_C$	Collector current (DC)		-	7	A
$I_B$	Base current (DC)		-	4	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25^\circ C$	-	60	W
$T_{sta}$	Storage temperature		-55	150	$^\circ C$
$T_j$	Junction temperature		-	150	$^\circ C$

**ELECTRICAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$I_{CBO}$	Collector-base cut-off current	$V_{CB}=400V$		5.0	mA
$I_{EBO}$	Emitter-base cut-off current	$V_{EB}=5V$		1.0	mA
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA$	150		V
$V_{CEsat}$	Collector-emitter saturation voltages	$I_C = 5.0A; I_B = 0.5A$		1.0	V
$h_{FE}$	DC current gain	$I_C = 2.0A; V_{CE} = 5V$	30		
$f_T$	Transition frequency at $f = 5MHz$	$I_C = 0.5A; V_{CE} = 10V$	10		MHz
$C_c$	Collector capacitance at $f = 1MHz$	$V_{CB} = 10V$			pF
$t_{on}$	On times	$I_C=5A, -I_{B(end)}=0.5A, V_{CC}=60V$			us
$t_s$	Turn-off storage time	$I_C=5A, -I_{B(end)}=0.5A, V_{CC}=60V$			us
$t_f$	Fall time	$I_C=5A, -I_{B(end)}=0.5A, V_{CC}=60V$		0.75	us